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(71) Applicant: **APPLIED MATERIALS, INC.** [US/US];
3050 Bowers Avenue, Santa Clara, CA 95054 (US).

(72) Inventors: **BALAKRISHNAN, Karthik**; 987 Bukit
Timah Road #03-16, Maple Woods, Singapore 589628
(SG). **PARK, Jung-rae**; 1710 Triton Court, Santa Clara, CA
95050 (US). **TAN, Xavier Zai, Yeong**; Choa Chu Kang
Street, 51 Block 527 #13-275, Singapore 680527 (SG). **AB-
HINAND, Sai**; 55 Strathmore Avenue #16-131, Singapore
140055 (SG). **PAPANU, James, S.**; 351 Holly Drive, San
Rafael, CA 94902 (US).

(74) Agent: **BERNADICOU, Michael, A.** et al.; Schwabe,
Williamson & Wyatt, P.C., 1211 SW 5th Avenue, Suite
1900, Portland, OR 97204 (US).

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(54) Title: AUTOMATIC KERF OFFSET MAPPING AND CORRECTION SYSTEM FOR LASER DICING

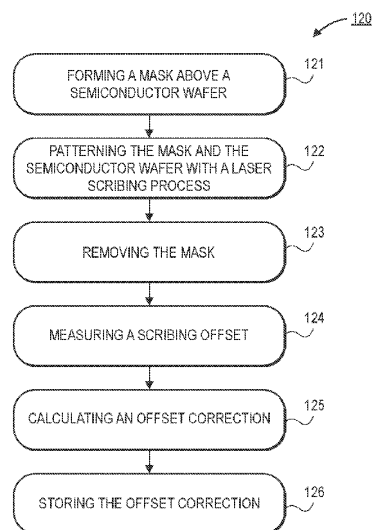


FIG. 1

(57) Abstract: Embodiments of the present disclosure include methods of determining scribing offsets in a hybrid laser scribing and plasma dicing process. In an embodiment, the method comprises forming a mask above a semiconductor wafer. In an embodiment, the semiconductor wafer comprises a plurality of dies separated from each other by streets. In an embodiment, the method further comprises patterning the mask and the semiconductor wafer with a laser scribing process. In an embodiment, the patterning provides openings in the streets. In an embodiment, the method further comprises removing the mask, and measuring scribing offsets of the openings relative to the streets.

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